MSKSEMI 美森科













ESD

115

TSS

MOV

GDT

PIFD

SGM3157-MS

Product specification





General Description

The SGM3157-MS is an advanced CMOS analog switch fabricated with silicon gate CMOS technology. It achieves very low propagation delay while maintaining CMOS low power dissipation. Analog and digital voltages that may vary across the full power-supply range (from Vcc to GND).

The Select pin has over voltage protection that allows voltages above Vcc, up to 7.0 V to be present on the pin without damage or disruption of operation of the part, regardless of the operating voltage.

Features

- Low power dissipation
- High speed
- Standard CMOS logic levels
- High bandwidth, improved linearity
- Switches Standard NTSC/PAL Video, Audio, SPDIF and HDTV
- be used for Clock Switching, Data Mux'ing,etc.
- Low RDSON
- Break Before Make Circuitry, Prevents Inadver tent Shorts
- Operating temperature -55 °C ~ +125 °C
- package : SC70-6

Pinning and Marking

SC70-6	Pin Configuration	Marking
	B1 1 6 Select GND 2 5 Vcc B0 3 4 A	3157 *

Pin Description

Pin	I/O	Pin Function
A, B ₀ , B ₁	I/O	Data port
Select	1	Controlling choice
Vcc	1	Power supply port
GND	1	Ground

FUNCTIONS DESCRIPTION

Select input port	Function
L	B ₀ Connected to A
Н	B ₁ Connected to A



Order information

Orderable Device	Package	Packing Option
SGM3157-MS	SC70-6	3000PCS

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	-0.5 -+7.0	V
DC Switch Voltage (1)	Vs	-0.5-V _{CC} +0.5	V
DC Input Voltage (1)	V _{IN}	-0.5 -+7.0	V
DC Input Diode Current @ V _{IN} < 0 V	I _{IK}	-50	mA
DC Output Current	lout	128	mA
DC V _{CC} or Ground Current	Icc/I _{GND}	100	mA
Storage Temperature Range	Tstg	-65 -+150	$^{\circ}$ C
Junction Temperature Under Bias	TJ	150	$^{\circ}$ C
Junction Lead Temperature (Soldering, 10 Seconds)	T _L	260	$^{\circ}$ C
Power Dissipation @ +85°C	P _D	180	mW

NOTE:

Stresses beyond those listed under "ABSOLUTE MAXIMUM RATINGS" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

1. The input and output negative voltage ratings may be exceeded if the input and output diode current ratings are observed.

CAUTION

This integrated circuit can be damaged by ESD if you don't pay attention to ESD protection. QCSEMI recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

QCSEMI reserves the right to make any change in circuit design, specification or other related things if necessary without notice at any time. Please contact sales office to get the latest datasheet.

RECOMMENDED OPERATING CONDITIONS (2)

Cha	Symbol	Min	Max	Unit		
Supply Voltage Operating		V _{cc}	1.65	5.5	V	
Select Input Voltage	V _{IN}	0	V _{CC}	V		
Switch Input Voltage	V _{IN}	0	V _{CC}	V		
Output Voltage	V _{OUT}	0	V _{cc}	V		
Operating Temperature		T _A	-55	+125	$^{\circ}$	
Input Rise and Fall Time	Control Input $V_{CC} = 2.3 \text{ V} \sim 3.6 \text{ V}$	tr tf	0	10	A /	
iliput Kise aliu Fali Tilile	Control Input $V_{CC} = 4.5 \text{ V} \sim 5.5 \text{ V}$	tr,tf	0	5.0	ns/V	

Note:

2. Select input must be held HIGH or LOW, it must not float



ELECTRICAL CHARACTERISTICS

					Γ _A = 25℃		T _A = -40°	C ~ +85℃	
Symbol	Parameter	Test Conditions	V _{cc}	Min	Тур	Max	Min	Max	Unit
DC ELEC	TRICAL CHARAC	TERISTICS	1						
			1.65 ~ 1.95				0.75Vcc		
V _{IH}	High Level Input		2.3 ~ 2.8				1.5		V
VIH	Voltage		3 ~ 4.2				2.4		
			4.5 ~ 5.5				0.6Vcc		
			1.65 ~ 1.95					0.25V _{CC}	
V _{IL}	Low Level Input Voltage		2.3 ~ 2.8					0.4	V
			3 ~ 5.5					0.3Vcc	
I _{IN}	Input Leakage Current	0 < V _{IN} < 5.5 V	0 ~ 5.5		±0.05	±0.1		±1	μA
I _{OFF}	OFF State Leakage Current	0 < A, B < Vcc	1.65 ~ 5.5		±0.05	±0.1		±1	μA
I _{cc}	Quiescent Supply	V _{IN} = Vcc or GND I _{OUT} = 0	5.5			1.0		10	μA
	Analog Signal Range		V _{cc}	0		V _{CC}	0	V _{CC}	\ \
		V _{IN} = 0 V, I _O = 30 mA			3.0			7.0	Ω
		$V_{IN} = 2.4 \text{ V},$ $I_{O} = -30 \text{ mA}$	4.5		5.0			12	Ω
		$V_{IN} = 4.5 \text{ V},$ $I_{O} = -30 \text{ mA}$			7.0			15	Ω
	Switch On	V _{IN} = 0 V, I _O = 24 mA	3.0		4.0			9.0	Ω
R _{ON}	Resistance ⁽³⁾	$V_{IN} = 3 V$, $I_{O} = -24 \text{ mA}$	3.0		10			20	Ω
		$V_{IN} = 0 V$, $I_O = 8 \text{ mA}$	2.3		5.0			12	Ω
		$V_{IN} = 2.3 \text{ V},$ $I_{O} = -8 \text{ mA}$	2.3		13			30	Ω
		V _{IN} =0V, I _O =4 mA			6.5			20	Ω
		V _{IN} = 1.65 V, I _O = -4 mA	1.65		17			50	Ω
	On Resistance	$I_A = -30 \text{ mA}$ $0 \le V_{Bn} \le V_{CC}$	4.5					25	Ω
R _{RANGE}	Over Signal Range ⁽³⁾⁽⁷⁾	$I_{A} = -24 \text{ mA}$ $0 \le V_{Bn} \le V_{CC}$	3					50	Ω



ELECTRICAL CHARACTERISTICS (continued)

O mark at	D	T	.,		T _A = 25°	C	T _A = -40	°C ~ +85°C	1114	
Symbol	Parameter	Test Conditions	V _{cc}	Min	Тур	Max	Min	Max	Unit	
D	On Resistance Over Signal	$I_A = -8 \text{ mA}$ $0 \le V_{Bn} \le V_{CC}$	2.3					100	Ω	
R _{RANGE}	Range ⁽³⁾⁽⁷⁾	$I_{A} = -4 \text{ mA}$ $0 \le V_{Bn} \le V_{CC}$	1.65					300	Ω	
		I _A = -30 mA V _{Bn} = 3.15	4.5		0.15				Ω	
ΔR _{ON}	On Resistance	I _A = -24 mA V _{Bn} = 2.1	3		0.2				Ω	
ΔINON	Match Between Channels (3)(4)(5)	I _A = -8 mA V _{Bn} = 1.6	2.3		0.5				Ω	
		I _A = -4 mA V _{Bn} = 1.15	1.65		0.5				Ω	
		$I_A = -30 \text{ mA}$ $0 \le V_{Bn} \le V_{CC}$	5		6.0				Ω	
В	On Resistance	$I_A = -24 \text{ mA}$ $0 \le V_{Bn} \le V_{CC}$	3.3		12				Ω	
R _{FLAT}	Flatness ⁽³⁾⁽⁴⁾⁽⁶⁾	$I_A = -8 \text{ mA}$ $0 \le V_{Bn} \le V_{CC}$	2.5		28				Ω	
		$I_A = -4 \text{ mA}$ $0 \le V_{Bn} \le V_{CC}$	1.8		125				Ω	
AC ELECT	RICAL CHARAC	TERISTICS								
			1.65 ~ 1.95						nS	
t_{PHL}	Propagation	Figure 1	2.3 ~ 2.7					1.2	nS	
t_{PLH}	Delay Bus to Bus ⁽⁸⁾	V _I = OPEN	3.0 ~ 3.5					0.8	nS	
				4.5 ~ 5.5					0.3	nS
	Output Enable	Figure 1	1.65 ~ 1.95			23	7.0	24	nS	
$t_{\sf PZL}$	Time,	$V_1 = 2*V_{CC}$ for	2.3 ~ 2.7			13	3.5	14	nS	
t_{PZH}		$t_{PZL}, V_{I} = 0 \text{ V for}$ t_{PZH}	3.0 ~ 3.5			6.9	2.5	7.6	nS	
	(7 to Bil)	ΨZH	4.5 ~ 5.5			5.2	1.7	5.7	nS	
	Output Disable	Figure 1	1.65 ~ 1.95			12.5	3.0	13	nS	
t_{PLZ}	Output Disable Time, Turn Off	Figure 1 $V_I = 2*V_{CC}$ for	2.3 ~ 2.7			7.0	2.0	7.5	nS	
t _{PHZ}	Time (A Port to B Port)	t_{PLZ} , $V_I = 0$ V for	3.0 ~ 3.5			5.0	1.5	5.3	nS	
	lo D i oitj	t _{PHZ}	4.5 ~ 5.5			3.5	0.8	3.8	nS	



ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions	V	T	a = 25°	2	T _A = -40℃	~ +85℃	Unit
Symbol	Parameter	rest conditions	V _{cc}	Min	Тур	Max	Min	Max	Onic
			1.65 ~ 1.95				0.5		nS
+	Break Before	Figure2,	2.3 ~ 2.7				0.5		nS
t _{B-M}	Make Time ⁽⁷⁾	$C_L = 50 \text{ pF}$, $R_L = 600 \Omega$	3.0 ~ 3.5				0.5		nS
		KL = 000 12	4.5 ~ 5.5				0.5		nS
	Charge Injection	Figure 3, $C_L = 0.1 \text{ nF}$,	5.0		7.0				рC
Q	(7)	$V_{GEN} = 0 V$, $R_{GEN} = 0 \Omega$	3.3		3.0				pC
OIRR	Off Isolation (9)	Figure 4, R _L = 50 Ω , f = 10MHz	1.65 ~ 5.5		-57				dB
Xtalk	Crosstalk	Figure 5, R_L = 50 Ω , f = 10MHz	1.65 ~ 5.5		-54				dB
BW	-3 dB Bandwidth	Figure 8, $R_L = 50 \Omega$	1.65 ~ 5.5		350M				Hz
THD	Total Harmonic Distortion ⁽⁷⁾	$R_L = 600 \Omega,$ $0.5V_{P-P}$ $f = 600 Hz \sim 20$ kHz	5.0		0.011				%
C_{IN}	Select Pin Input Capacitance (10)		0		2.3				pF
C _{IO-B}	B Port Off Capacitance (10)	Figure 6	5.0		5.0				pF
C _{IOA-ON}	A Port Capacitance when Switch is Enabled (10)	Figure 7	5.0		15.5				pF



Note:

- 3. Measured by the voltage drop between A and B pins at the indicated current through the switch. On Resistance is determined by the lower of the voltages on the two (A or B Ports).
- 4. Parameter is characterized but not tested in production.
- 5. $\Delta R_{ON} = R_{ON}$ max R_{ON} min measured at identical V_{CC} , temperature and voltage levels.
- 6. Flatness is defined as the difference between the maximum and minimum value of On Resistance over the specified range of conditions.
- 7. Guaranteed by Design.
- 8. This parameter is guaranteed by design but not tested. The bus switch contributes no propagation delay other than the RC delay of the On Resistance of the switch and the 50 pF load capacitance, when driven by an ideal voltage source (zero output impedance).
- 9. Off Isolation = 20 log10 $[V_A/V_{Bn}]$.
- 10. T_A = +25°C, f = 1 MHz, Capacitance is characterized but not tested in production.

TEST CIRCUITS

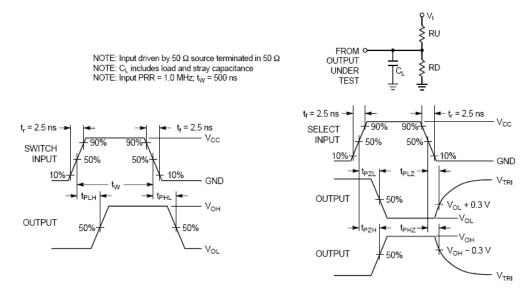


Figure 1. AC Test Circuit ,AC Waveforms

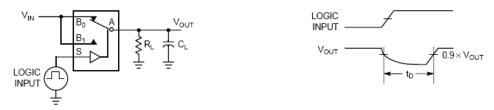


Figure 2. Break Before Make Interval Timing



TEST CIRCUITS (continued)

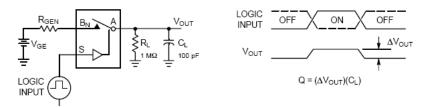


Figure 3. Charge Injection Test

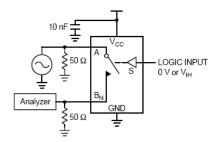


Figure 4. Off Isolation

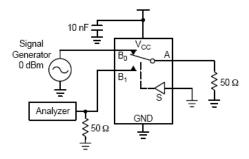


Figure 5.Crosstalk

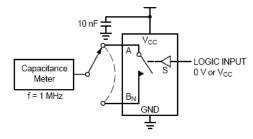


Figure 6. Channel Off Capacitance



TEST CIRCUITS (continued)

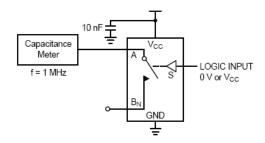


Figure 7. Channel On Capacitance

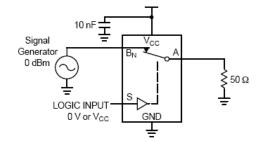
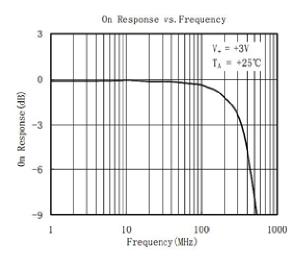
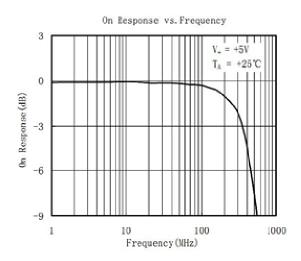


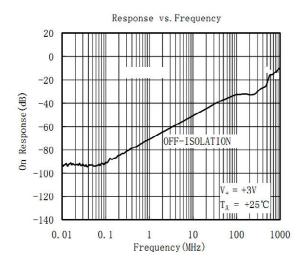
Figure 8. Bandwidth

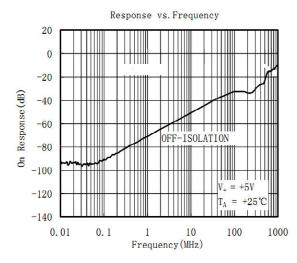


TYPICAL PERFORMANCE CHARACTERISTICS





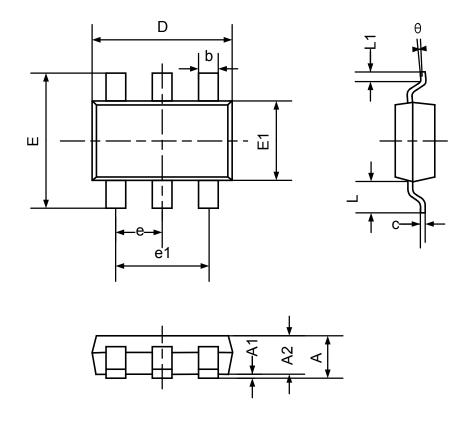






PACKAGE OUTLINE

SC70-6



Cumbal	Dimensions in Millimeters					
Symbol	Min	Max				
А	0.85	1.05				
A1	0.00	0.10				
A2	0.80	1.00				
b	0.15	0.35				
С	0.08	0.22				
D	2.02	2.12				
E	2.20	2.40				
E1	1.25	1.35				
е	0.65BSC					
e1	1.30BSC					
L	0.50REF					
L1	0.28 0.38					
θ	0° 8°					



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